

ABSTRACT

[00031] A method of etching high dielectric constant materials using halogen gas and reducing gas chemistry. An embodiment of the method is accomplished using a 20 to 300 sccm of chlorine and 2 to 200 sccm of carbon monoxide, regulated to a total chamber pressure of 2-100 mTorr to etch a hafnium oxide layer.

1002795.030602